



Role of dual SiO_x:H based buffer at the p/i interface on the performance of single junction microcrystalline solar cells



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ABSTRACT

In p-i-n structure a-Si solar cell a buffer layer with proper characteristics plays important role in improving the p/i interface of the cell, reducing mismatch of band gaps and number of recombination centres. However for p-i-n structure microcrystalline (μ -Si:H) cell which has much less light induced degradation than a-Si:H cell, not much work has been done on development of proper buffer layer and its application to μ -Si:H cell. In this paper we have reported the development of two intrinsic oxide based microcrystalline layer having different characteristics for use as buffer layers at the p/i interface of μ -Si:H cell. Previously SiO_x:H buffer layer has been used at the p/i interface which showed positive effects. To explore the possibility of improving the performance of p-i-n structure μ -Si:H cell further we have thought it interesting to use two buffer layers with different characteristics at the p/i interface. The two buffer layers have been characterized in detail and applied at the p/i interface of the μ -Si:H cell with positive effects on all the PV parameters mainly improves the open circuit voltage (V_{oc}) and enhances short circuit current (I_{sc}). The maximum initial efficiency obtained is 8.97% with dual buffer which is 6.7% higher than that obtained by using conventional single buffer layer at the p/i interface. Stabilized efficiency of the cell with dual buffer is found to be \sim 9.5% higher than that with single buffer after 600 h of light soakings.

1. Introduction

Amongst silicon based thin film solar cells micromorph has good potential of competing with c-Si cells when the production volume is in the terawatt range and the stabilized module efficiency of micromorph is 15% and above. In a micromorph cell the microcrystalline (μ -Si:H) cell is the bottom and a-Si cell is the top cell. The bottom cell shows very little light induced integration [1–4] which is its basic advantage. To improve the performance of μ -Si:H cell is therefore now a priority area in photovoltaic (PV) cell research and development activities.

One of the major downside of the single junction μ -Si:H solar cell is its low open circuit voltage as compared to a-Si silicon solar cell [5,6]. Although there is a large impact of crystalline volume fraction on V_{oc} of the μ -Si:H solar cell, carrier recombination at the p-i interface region plays a considerable role to minimize V_{oc} of the cell. Comprehensive research is going on to overcome the drawbacks. Various approaches have been taken to improve the V_{oc} . Use of a thin μ -Si:H buffer layer deposited by hot-wire chemical vapour deposition (HW-CVD) system was shown to significantly improve the V_{oc} in single junction μ -Si:H

solar cells [7,8]. Wide band gap window layer is one of common method to enhance the performance of single junction a-Si:H as well as μ -Si:H solar cell [9–12]. In recent times many other research activities is going on improve the performance of single junction μ -Si:H solar cell by various method [13–18].

In an earlier paper we have shown [19] the improvement in the performance of p-i-n structure a-Si solar cell by using intrinsic oxide based buffer layer at the p/i interface. For μ -Si:H Bugnon et al. have successfully used SiO_x:H buffer layer at the p/i interface of microcrystalline cell with positive results [20].

To obtain the beneficial effect of using buffer layer with proper characteristics we thought it worthwhile to employ double buffer layer with different characteristics to further improve the performance of microcrystalline cell. By using two buffer layers with proper characteristics we have been able to improve short circuit current and open circuit voltage of microcrystalline cell significantly. This new approach has given interesting results which can be explored further.

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2. Experimental details

Oxide based materials and single junction microcrystalline silicon solar cells are fabricated using capacitively coupled five chamber cluster RF-PECVD systems. We used 13.56 MHz rf- frequency for doped and oxide based layers and 27.12 MHz for intrinsic absorber layer. Semiconductor grade SiH₄, H₂, CO₂, B₂H₆, PH₃ gases were used to develop different layer of the solar cell. SiH₄, H₂, B₂H₆ and CO₂ gas were used to make oxide based p-layer with optimized process parameters. Flow ratio of CO₂ to SiH₄ (CO₂/SiH₄) was optimized with 0.5 for developing microcrystalline window layer. SiH₄, H₂ and CO₂ gases were employed to develop buffer layers and CO₂/SiH₄ of 0.4 and 0.25 were adopted to make a buffer of two different characteristics. We used the same chamber for developing p-layer and buffer layers for fabrication of solar cell. After making of window layer i.e. p-layer chamber was flushed with the H₂ plasma for 15 min followed by a thin a-Si coating by SiH₄ and H₂ to decontaminate the chamber. Intrinsic absorber layer (i-μc-Si: H) was developed in separate chamber in high power pressure regime with the help of SiH₄ and H₂. 1% PH₃ in SiH₄ and H₂ gases were used to develop n-type films.

The films are deposited on Na/K free Schott glass and one side polished silicon wafer for various characterizations. Stylus type profilometer (Bruker Dektak-XT) was used to measure the thicknesses of the films. Dark conductivity (σ_d) was measured at room temperature in a cryostat evacuated at the range of $\sim 10^{-5}$ Torr, after making co-planar metal electrode of aluminum deposited by thermal evaporation. The conductivity was calculated using the formula:

$$\sigma_d = (w \times I) / (l \times d \times V) \quad (1)$$

where l = length of the electrode, d = film thickness, w = separation between two electrodes, I = Current and V = applied voltage. Activation energy (E_a) was calculated from the slope of $\ln \sigma_d$ vs $10^3/T$ plot [19]. Atomic Force Microscopy (NT-MDT) and High Resolution-Transmission Electron Microscopy studies ((HRTEM JEOL-JSM 20100) are employed to explore the structural properties of the films. The crystalline volume fraction (X_c) of the films was estimated using Raman spectroscopy (Lab RAM HR-Argon ion laser, wavelength-514 nm in back scattering geometry). X_c was calculated from the integrated intensities of Raman peak at 480 cm⁻¹, 510 cm⁻¹ and 520 cm⁻¹ using the formula,

$$X_c = (I_{510} + I_{520}) / (I_{480} + I_{510} + I_{520}) \quad (2)$$

The XRD analysis of the micro/nano crystalline materials was procured by a high resolution X-ray diffractometer (PANALYTICAL XPERT PRO). Perkin-Elmer Spectrum Two spectrometer in absorption mode was used to accomplished FTIR spectroscopy. Atomic percent of oxygen C(O) incorporated in the film was estimated from the integrated absorption strength of Si-O-Si stretching absorption band around 900–1200 cm⁻¹ following Lucovsky *et al.* [21]. Optical gap of microcrystalline material can be often expressed as the photon energy at which absorption coefficient (α) = 10^4 cm⁻¹ which is also known as E_{04} . The optical absorption (E_{04}) was evaluated from UV-visible spectroscopic data.

I - V characteristics of all the fabricated solar cell have been measured under standard test conditions i.e. at AM 1.5 G, 30 °C and 1000 W/m² and spectral response was measured in Bentham PVE300 setup.

3. Results and discussions

3.1. Material characterizations

Optimized process parameters for deposition of microcrystalline p-SiO_x:H, intrinsic absorber and n-type layer is shown in Table 1. High quality intrinsic layer [22] of microstructure factor (r) = 0.038, calculated after deconvolution of the FTIR spectrum at 2000 cm⁻¹ and around 2070–2090 cm⁻¹ respectively [23] using the formula,

$$r = I_{2070} / (I_{2000} + I_{2070}) \quad (3)$$

was used as active layer. FTIR spectrum of the intrinsic absorber layer is shown in Fig. 1.

Influence of CO₂/SiH₄ on the intrinsic buffer layer was investigated in details. Table 2 shows the process parameters for developing oxide based microcrystalline buffer layer with its optoelectronics and structural properties. As CO₂/SiH₄ = 0.5 was used to develop p-layer (described in Table 1), we evolved mso-1 layer with CO₂/SiH₄ = 0.4 and followed by 0.25 for mso-2 layer. From Fig. 2 it is clear that peak height around the 1000–1200 cm⁻¹ which is due to Si-O-Si bonding [21] increases gradually as we increase the CO₂/SiH₄ ratio for the deposited films. It can be seen that peak height is highest for p-layer followed by mso-1 and mso-2. It is also seen from Fig. 2 that with the decrease of CO₂/SiH₄, peak around the 2000 cm⁻¹ tends to increase which was good for solar cell application [24]. As a result of increasing peak height around 1000–1200 cm⁻¹, indicates the more amount of atomic oxygen (O) incorporated in the films microstructure, optical gap (E_{04}) of the p-μc-SiO:H layer is found to be highest which is 2.35 eV. E_{04} of mso-1 and mso-2 are 2.18 eV and 2.02 eV respectively which was shown in Fig. 3. From the absorption curve (Fig. 3) it is seen that optical gap of the intrinsic layer (i-μc-Si: H) is lowest among all which is 1.86 eV. From the Table 2, it is seen that dark conductivity (σ_d) of the films decreases from 1.1×10^{-4} S/cm (mso-1) to 3.0×10^{-5} S/cm (mso-2) as the CO₂/SiH₄ decreases from 0.4 to 0.25. This is due to defects introduced in the films if more atomic oxygen is incorporated which leads to greater disorder in the film resulting higher dark conductivity. But activation energy (E_a) increases to 0.49 eV from 0.41 eV as CO₂/SiH₄ decreases indicates the evolution of better quality microcrystalline films.

Raman spectroscopy analysis assists us to determine crystalline volume fraction (X_c) of the micro/nano crystalline films. X_c is calculated to be 51% for mso-1% and 62% for mso-2. As the O-content in mso-2 film is lower than the mso-1 film, X_c is higher for the film mso-1. It is clear indication that atomic oxygen hinders the growth of crystallinity [25]. That is why X_c increases as CO₂/SiH₄ decreases (Fig. 4). It could be also seen from the Fig. 4 that as CO₂/SiH₄ decreases peak point of the curve shifted towards the 520 cm⁻¹ which is the evidence of evolution of crystallites with larger grain size.

Fig. 5 shows the X-ray diffractogram of mso-1 and mso-2 films for a scattering angle between 25° and 60°. The XRD spectra shows three distinct peaks at $2\theta = 28.44^\circ$, 47.30° and 56.12° that correspond to the $\langle 111 \rangle$, $\langle 220 \rangle$ and $\langle 311 \rangle$ crystallographic planes of Si [26]. This indicates that the crystallites have grown on all possible direction. $\langle 111 \rangle$ and $\langle 220 \rangle$ peaks are more prominent than the $\langle 311 \rangle$ peaks. It is clear from the Fig. 5 that peak height around $\langle 111 \rangle$ and $\langle 220 \rangle$ are increases with decrease of CO₂/SiH₄ which is a clear indication of growth of more crystallites. The average size of the crystallites of these oxide based microcrystalline silicon films has been calculated using Debye-Scherrer formula [27]. As the CO₂/SiH₄ decreases from 0.4 to 0.25, average particle size increases to 14.4 nm from 11.7 nm which is probably due to more atomic oxygen in the films hamper the growth of crystallites in the films.

Microstructure, surface morphology and surface roughness of the intrinsic oxide based microcrystalline films have been investigated by AFM. Fig. 6 shows the AFM surface morphology of the i-μc-SiO:H films (mso-1 and mso-2). It is clear from the Fig. 6 that there is larger grain size noticed in mso-2 film as compare to mso-1 film. Average grain size is also estimated from the AFM micrograph and the results are agreed well with the grain size obtained from XRD analysis. RMS roughness of mso-2 films is also higher which is 77.36 nm rather than 39.61 nm for mso-1 layer. The more crystalline films have more roughness as a result light absorption will be more.

We have also compared the Raman spectra of the i-layers deposited without any seed layer, mso-1 and mso-2 as seed layer (Fig. 7). It is observed that high X_c of 66% of the i-layer grown on 5 nm of mso-2

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